

2 μm lasers and Mid-IR frequency conversion

June 26st 2015, ISLA Workshop, Munich

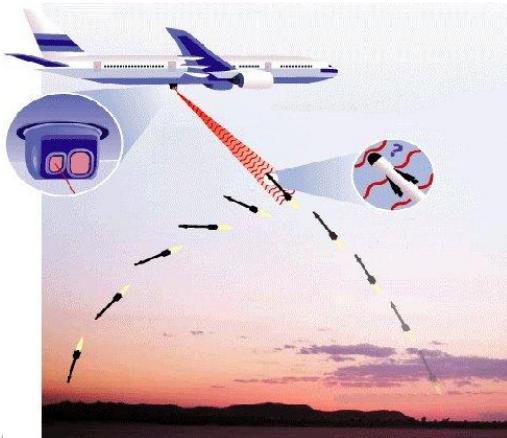
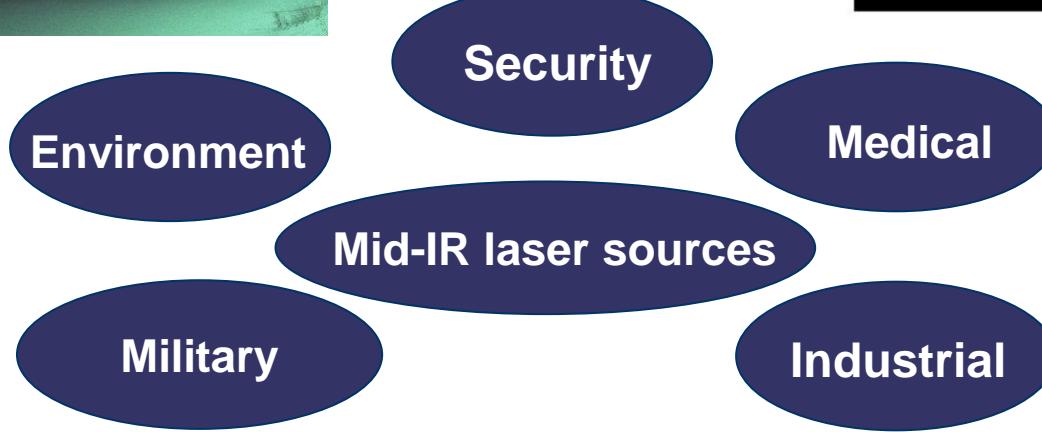
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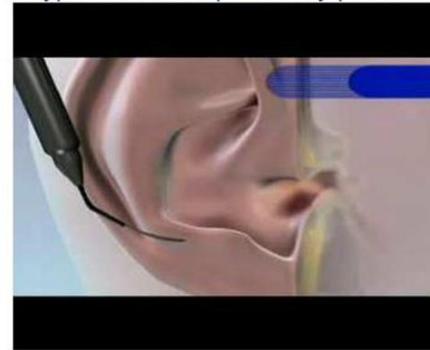
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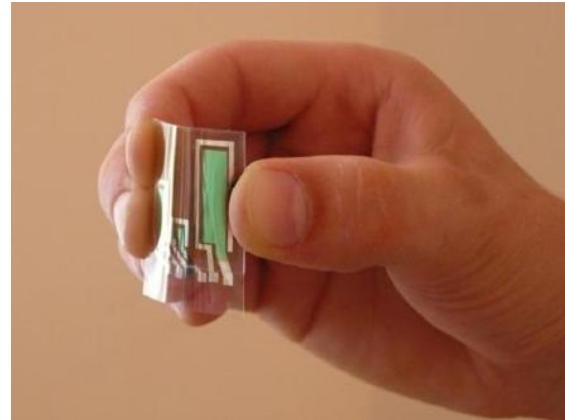
Mid-IR applications



Typical laser stapedotomy procedure



OmniGuide®
Driving smooth,
precise and safe laser



Thales Research and Techonology & MIR EC projects



<http://www.neo.no/village>



http://ec.europa.eu/research/transport/projects/items/casam_en.htm



www.mirifisens-project.eu

Security

Environment

Medical

Mid-IR laser sources

Military

Industrial



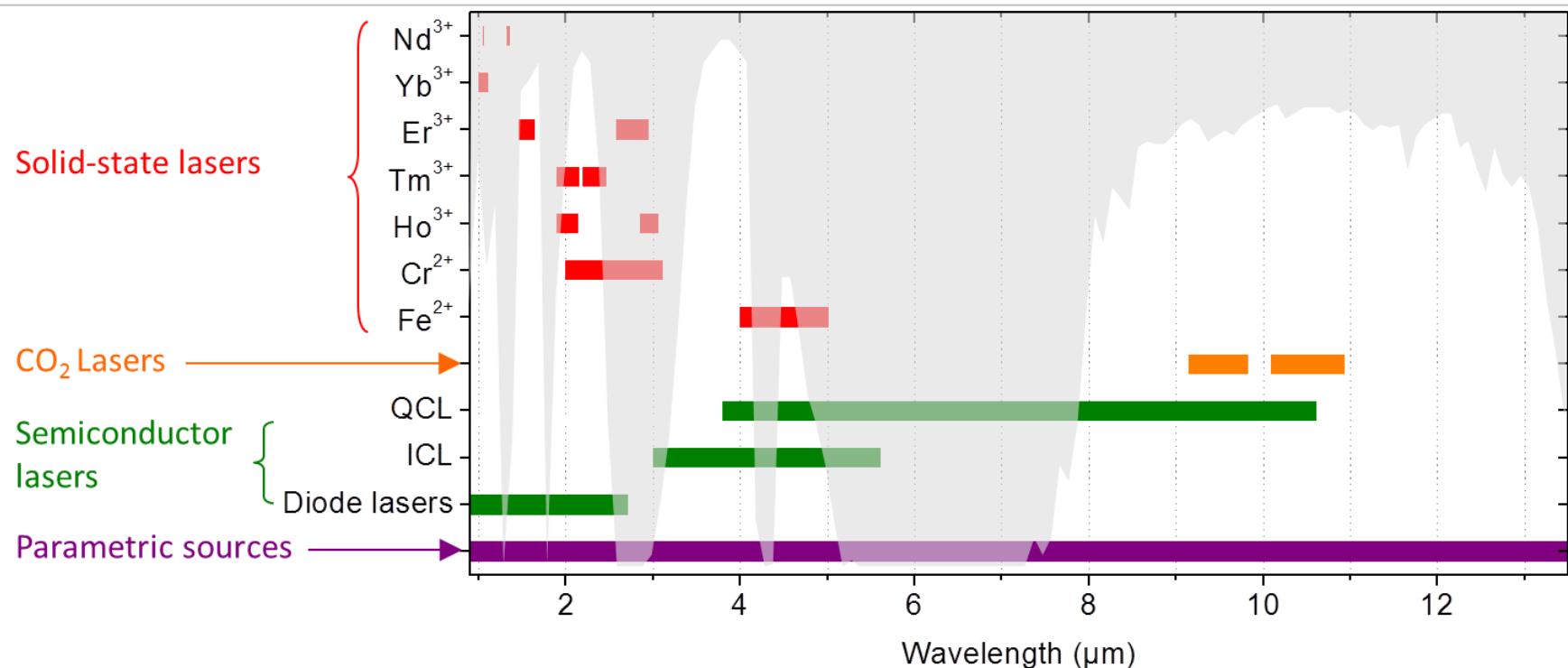
MIRSURG
<http://www.mirsurg.eu>



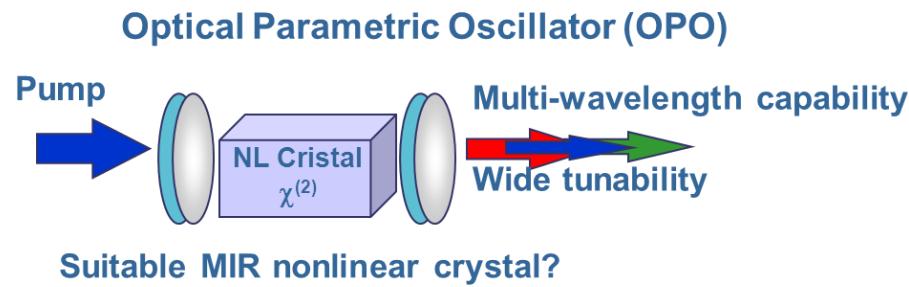
IMPROV
<http://www.fp7project-improv.eu>



MIR laser sources requirements and OPOs



- Parametric sources are still a promising option assuming 2 μm fiber laser pumping and NCPM efficient nonlinear crystal.



MWIR nonlinear crystals

Desirable properties for the NL crystal:

- High nonlinear coefficient
- Low absorption loss
- High laser damage threshold
- Low thermal lensing
- Non-critical phase matching

QPM vs BPM:

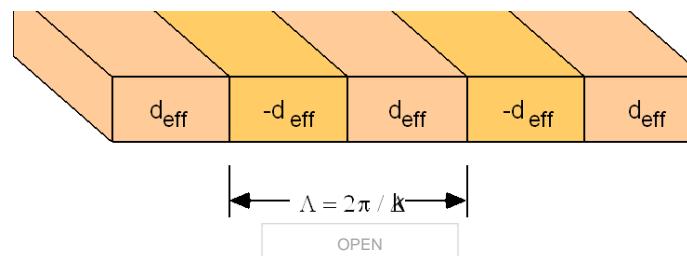
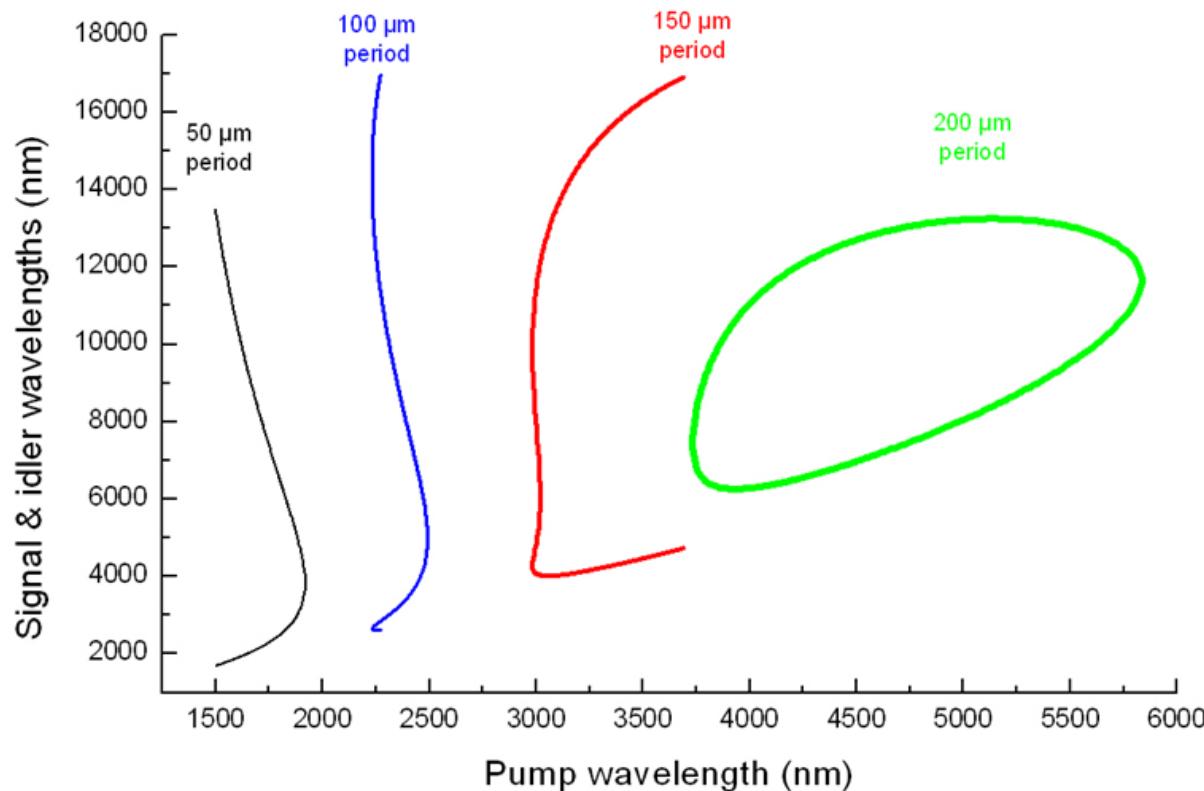
- High nonlinearities
- Non-critical interactions
- Engineering flexibility

	PPLN	ZGP	GaAs
<i>Transmission (μm)</i>	0.35-5	1-12	1-16
<i>Nonlinear Coefficient (pm/V)</i>	27	75	96
<i>Thermal Conductivity (W/m.K)</i>	5	35	52
α (cm ⁻¹) (> 2 μm)	--	0,025	0,02

OP-GaAs = PPLN of the MIR ?

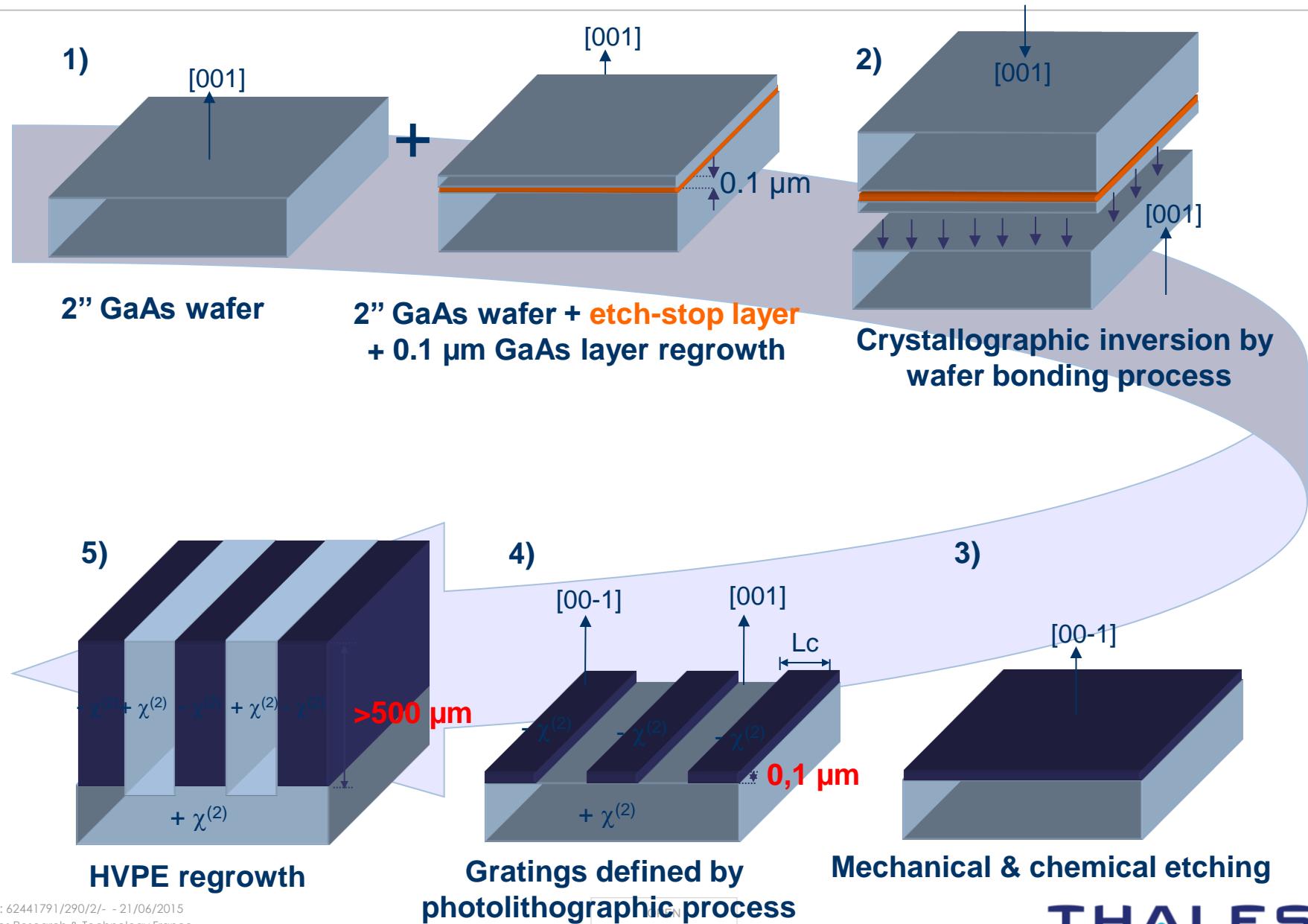
Quasi-Phasematching (QPM) in GaAs

- Periods under 100 µm for near-infrared pump lasers



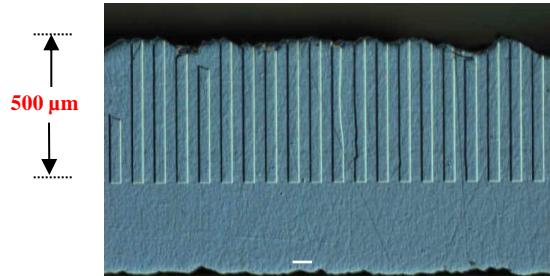
Fabrication of Thick Orientation-Patterned GaAs

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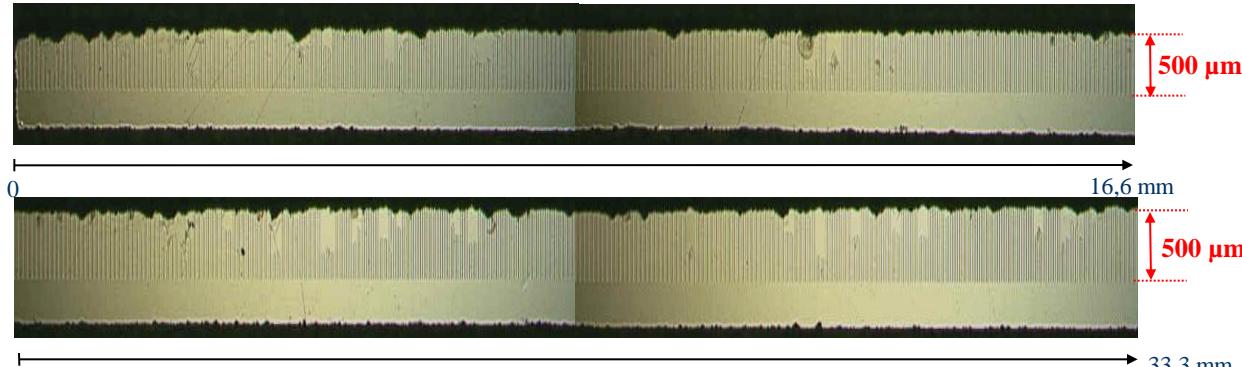
Full wafer growth

2" multigrating 500 μm thick OP-GaAs



Growth characteristics:

- **Growth rates:**
 $v(113) = 33 \mu\text{m/h}$
 $v(-112) = 30 \mu\text{m/h}$
- **4 growth interruptions**



Cross section of a 3 cm-long OP-GaAs sample (63 μm grating period)

Losses down to 0.016 cm^{-1} at 2 μm (< 0.03 cm^{-1} in average)

Difference Frequency Generation

DFG at around 7.8 μm from Er and Tm CW fiber lasers : UoDusseldorf & ORC
(S. Vasilyev et al., Opt. Lett., 33, 13, 2008, pp. 1413-15)

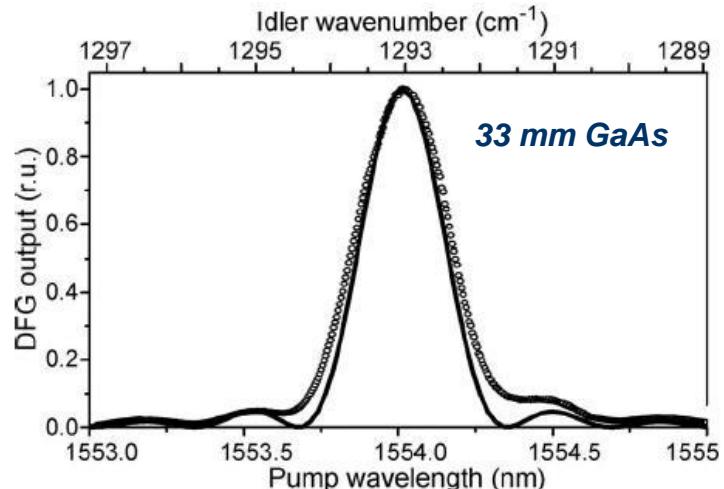


Fig. 2. Measured (°) and calculated (solid curve) DFG output versus signal wavelength.

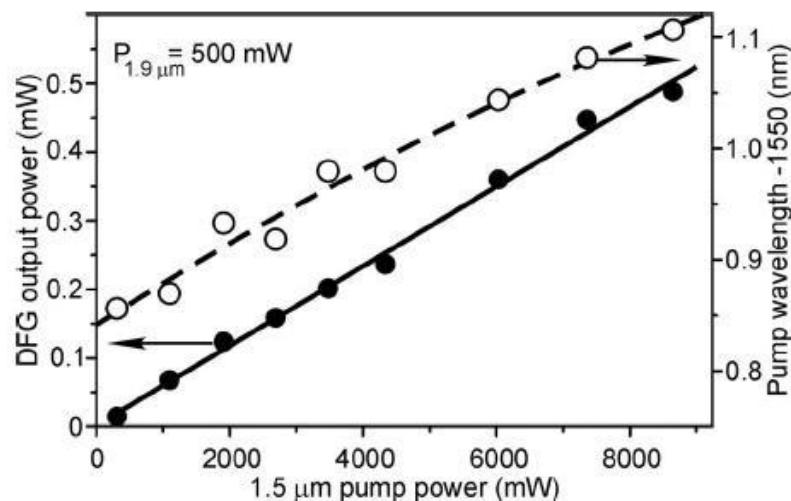
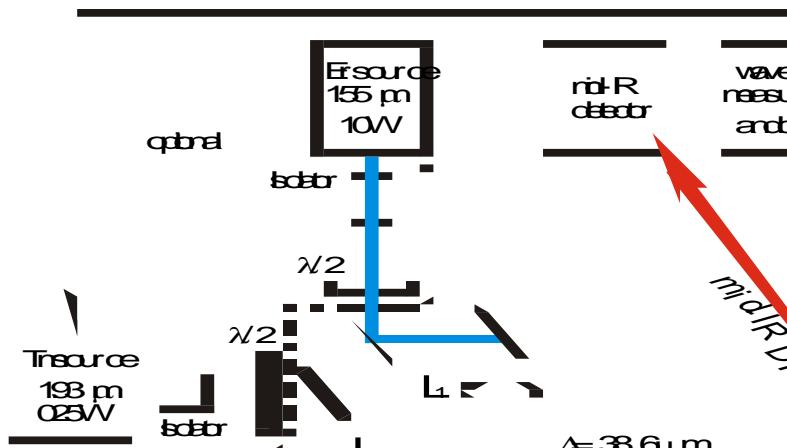
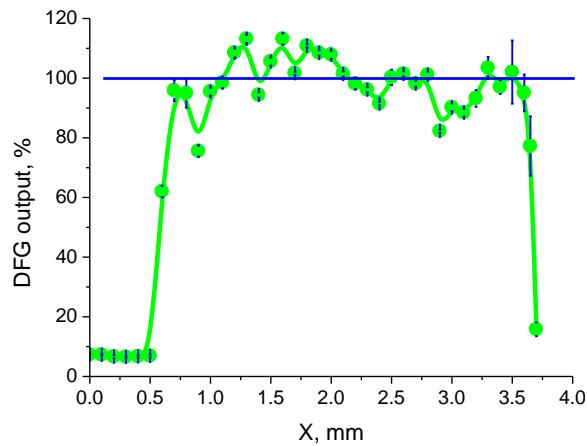


Fig. 3. DFG output power (•) and optimal pump (°) wavelength versus pump power.

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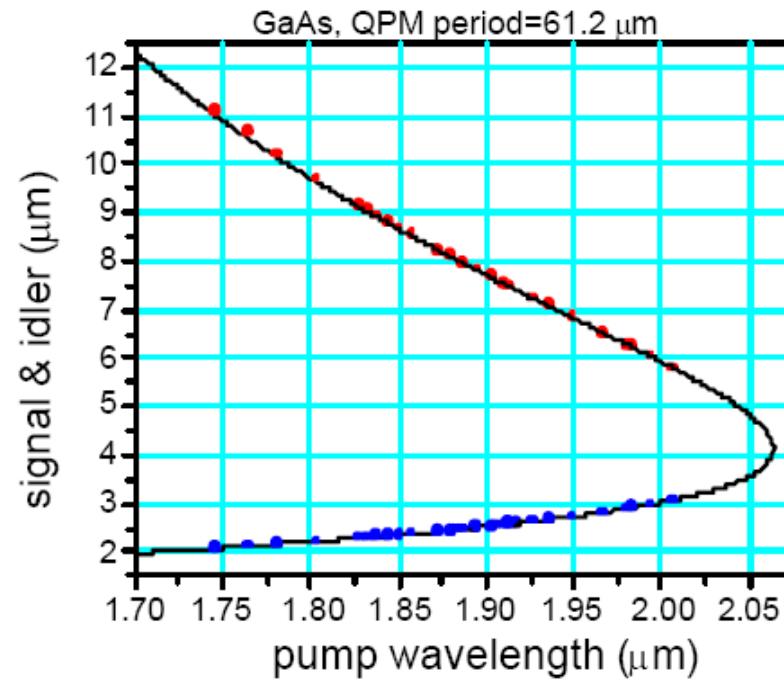
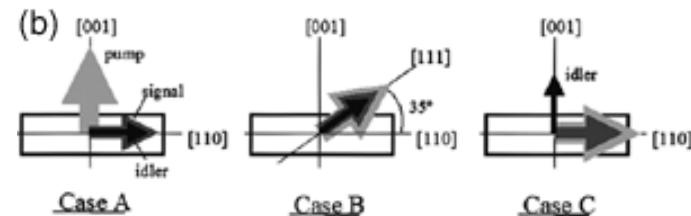
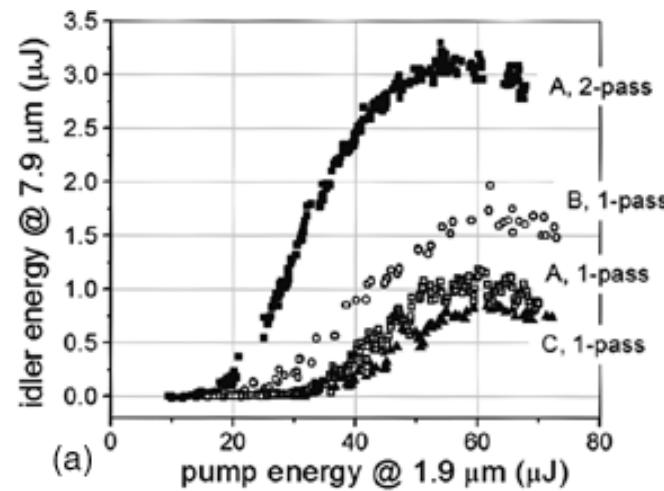
Optical Parametric Oscillation

✓ First demonstration of GaAs OPO (2004): Stanford University & Thales

(K.L Vodopyanov et al., Optics Letters, Vol 29, 16 (2004))



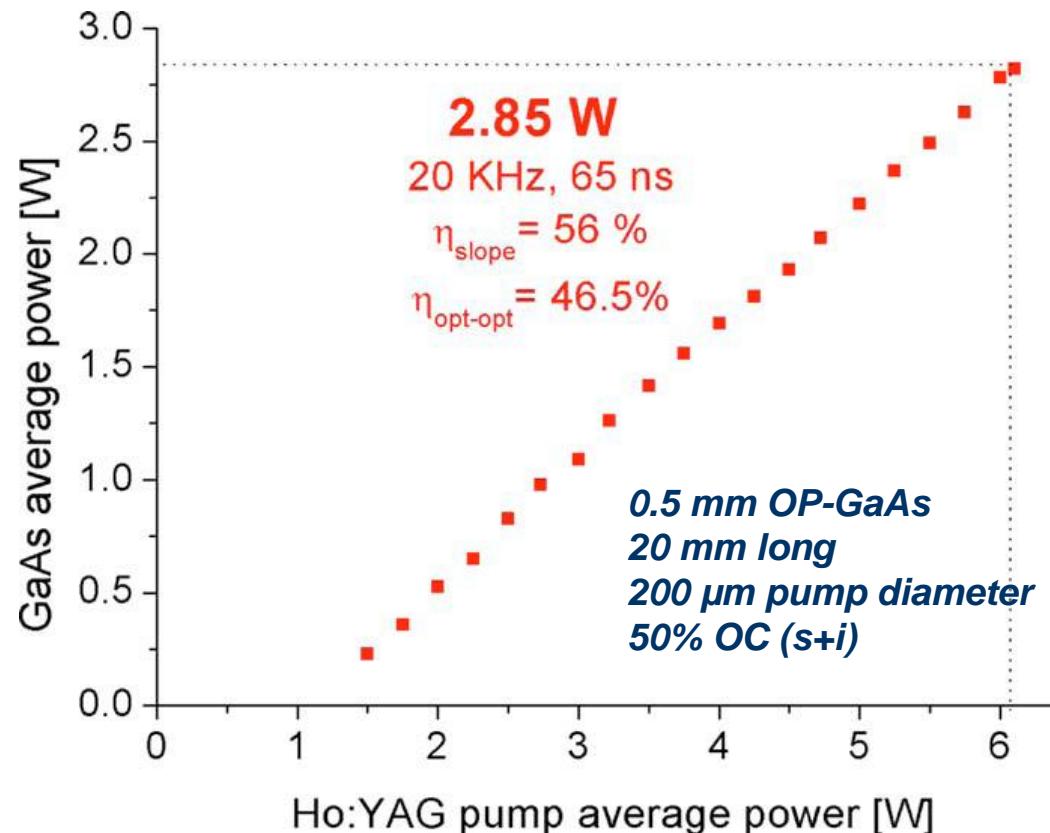
- OP-GaAs sample length: 13 mm
- HVPE layer thickness: 500 μm
- PPLN OPO pump



High power OPO

✓ High power GaAs OPO (2008): Institut St. Louis (ISL)
(C. Kieleck et al., Optics Letters, Vol 34, 3 (2009))

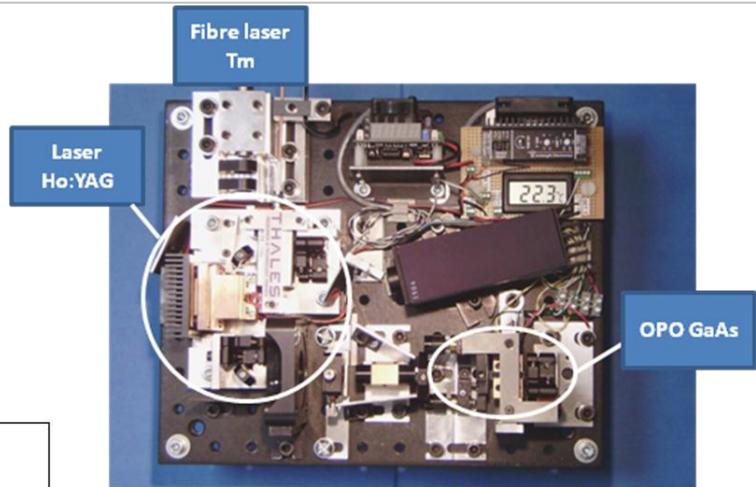
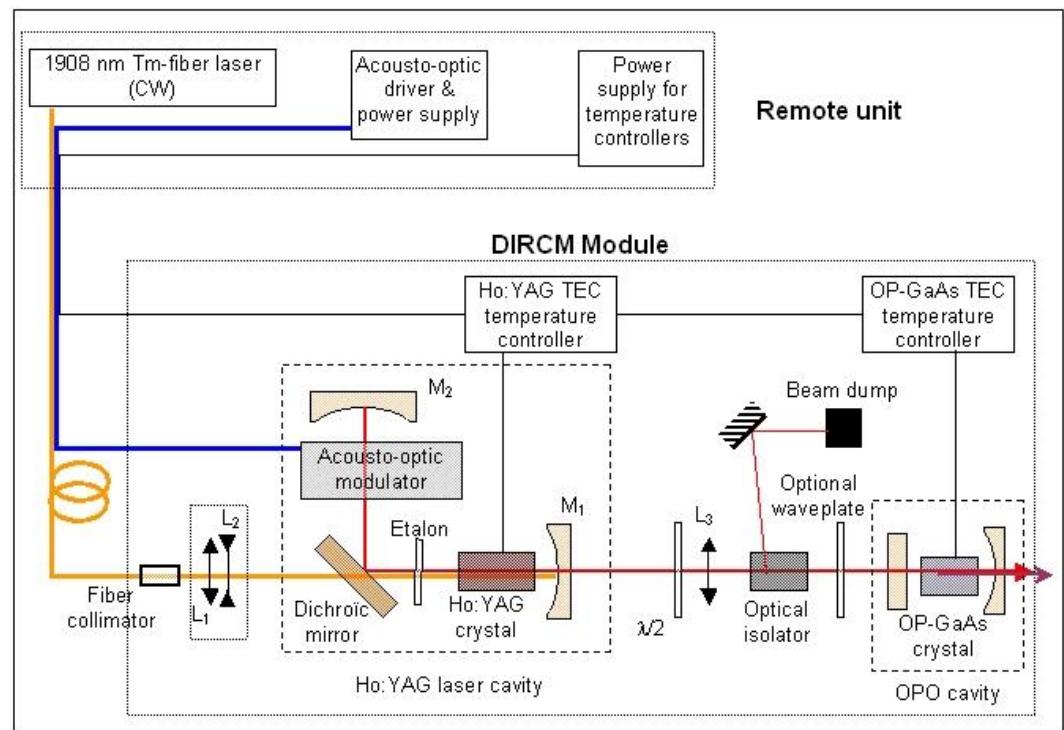
- >2.09 μm high rep.rate Ho:YAG pump , 3-5 μm emission.
- >Up to 60% slope efficiency and 2.85 W output
- >Efficiency comparable to ZnGeP₂



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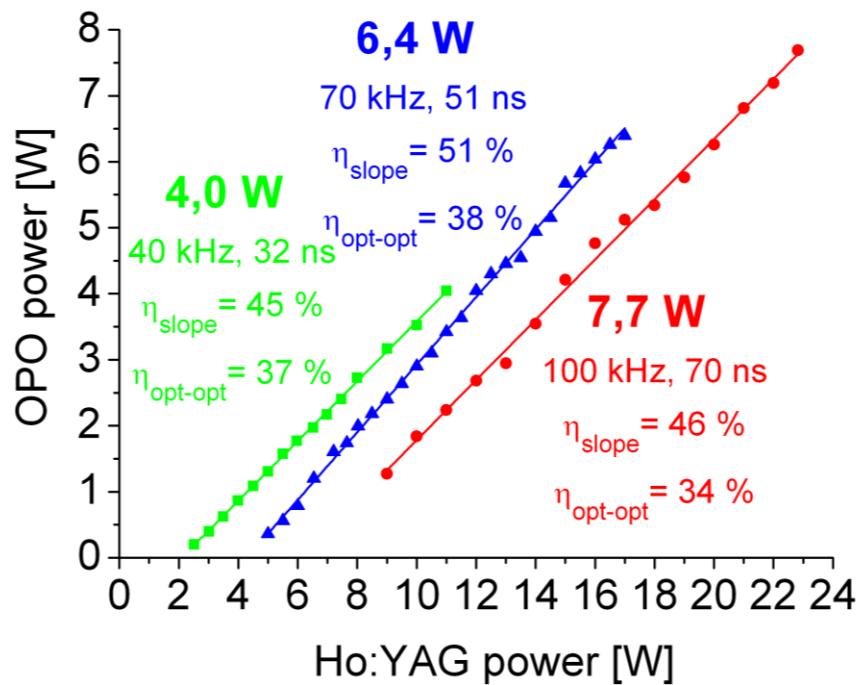
Portable DIRCM module

- > 20 W Tm fiber laser
- > 10 W Q-switched Ho:YAG
- > 3.0 W MWIR at 40 kHz
- > $M^2 = 1.4$



Higher power experiments

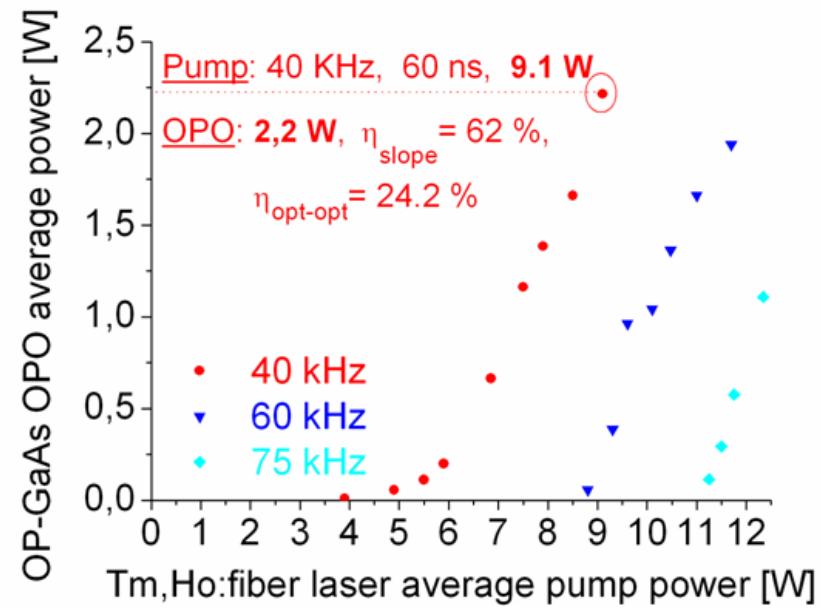
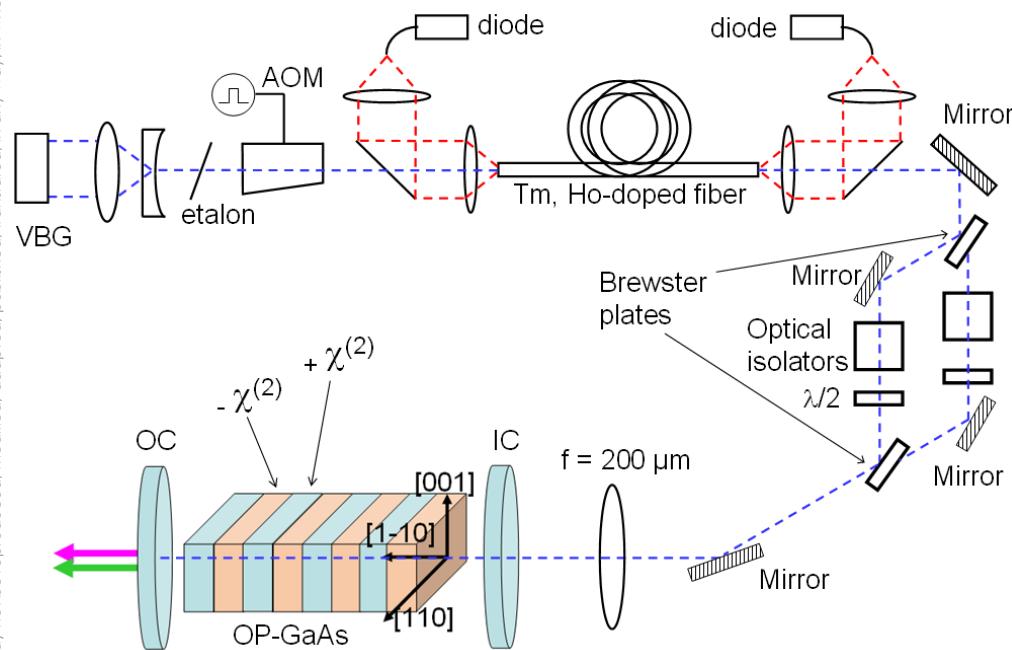
- > 25 W Q-switch Ho:YAG laser
- > 20 mm long crystal, 0.45 mm thick
- > 7.7 W at 100 kHz in 3-5 μm range (pump limited)
- > $M^2 < 1.4$ (signal) & 1.8 (idler)



Box dimensions :
391 x 516 mm

Fiber laser pumping

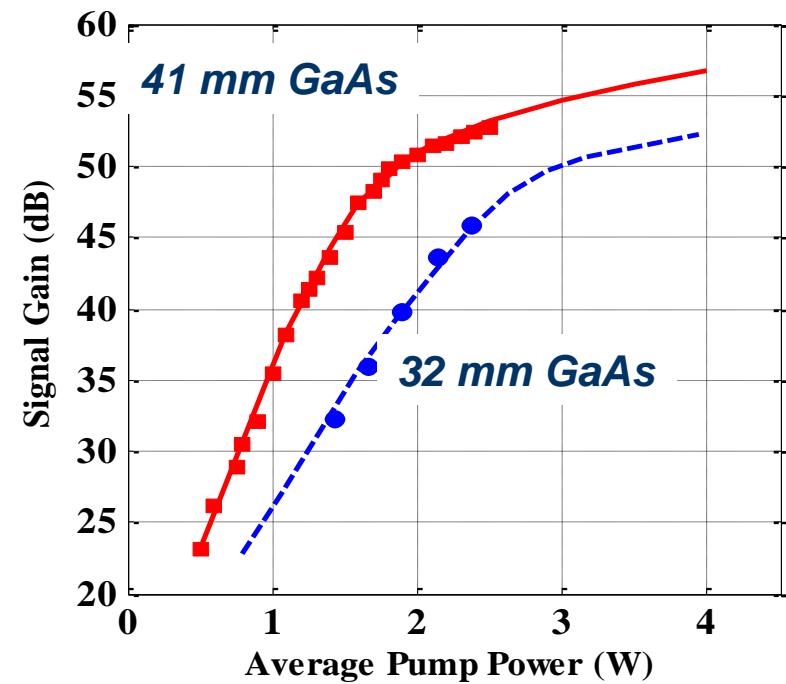
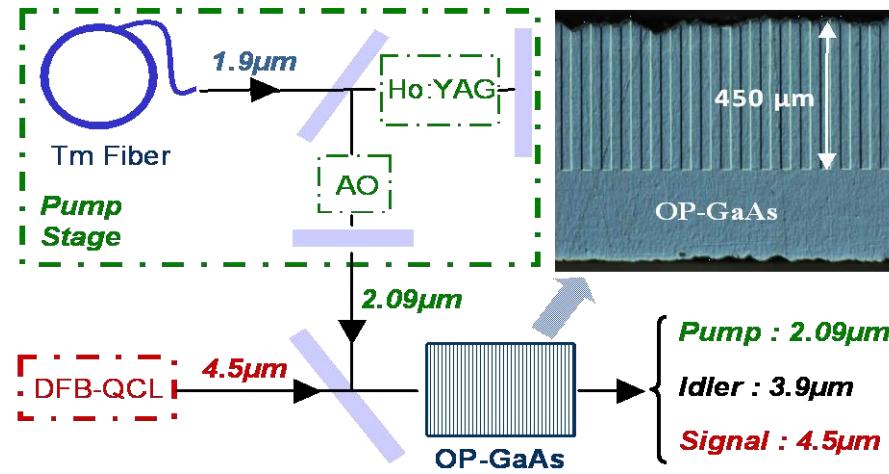
- > Q-switched Tm:Ho fiber laser
- > 2.2 W output power at 40 kHz
- > Pump peak power limitation



C. Kieleck, et al., Proc. SPIE 7582 (2010)

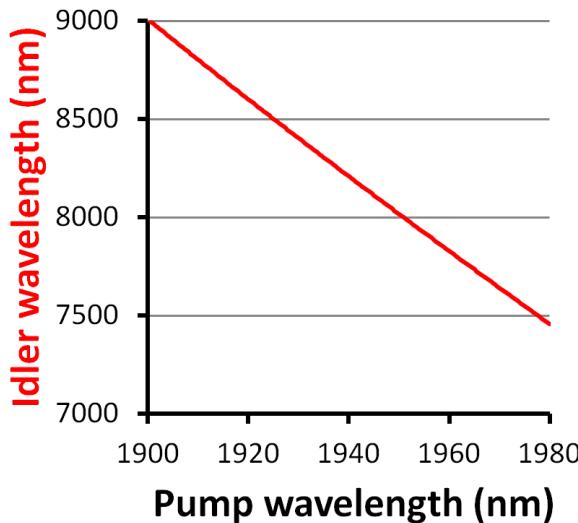
Parametric amplification of a 4.5 μm DFB QCL

- > 3 mW 4.5 μm CW DFB QCL
- > 2.09 μm Ho:YAG 30 ns pulsed pump at 20 kHz
- > 53 dB gain with 41 mm long GaAs crystal
- > 600 W peak power
- > $M^2 = 1.3$, $\Delta\lambda < 0.5$ nm (instr. limited)

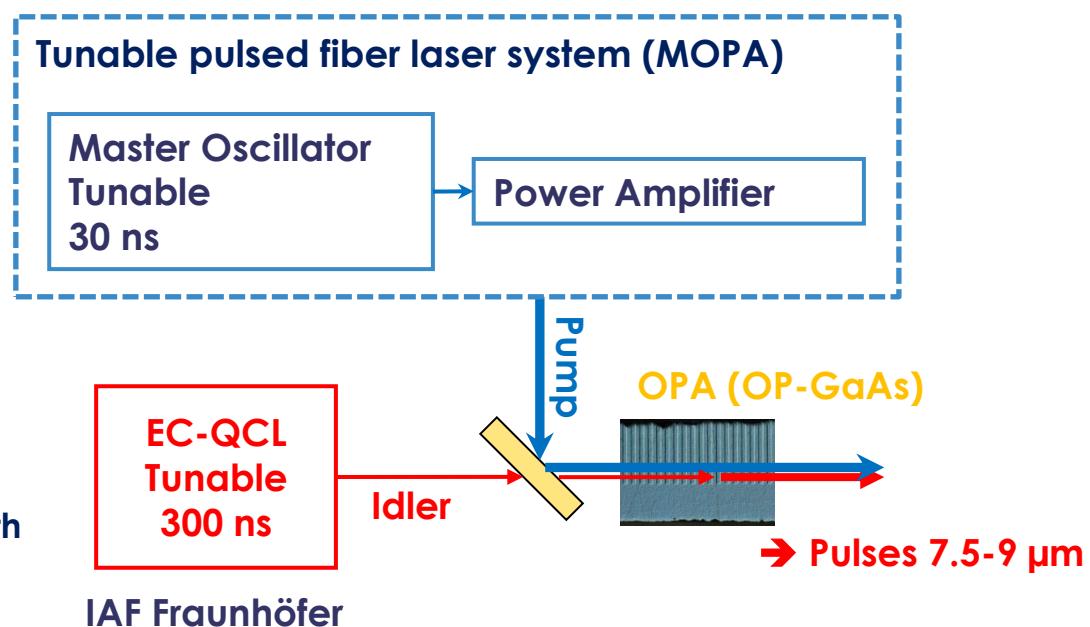


G. Bloom et al., Optics Letters, Vol.35, N 4, (2010).

7-9 μ m tunable parametric amplification

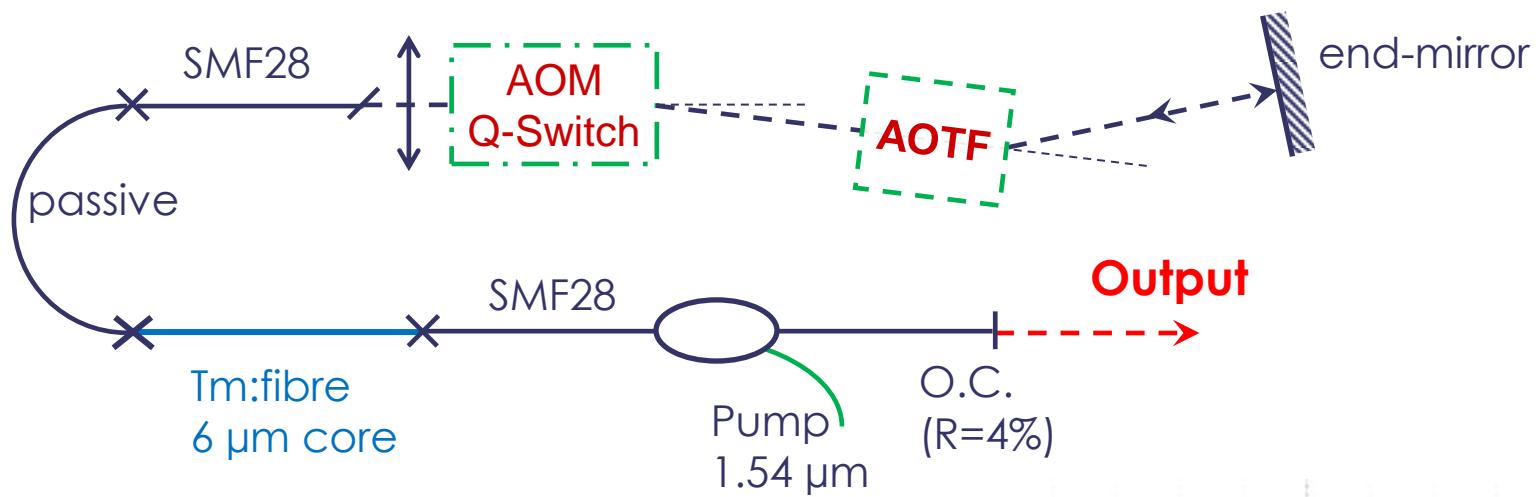


Amplified wavelength vs pump wavelength
for a fixed QPM period of 65.8 μ m at room
temperature

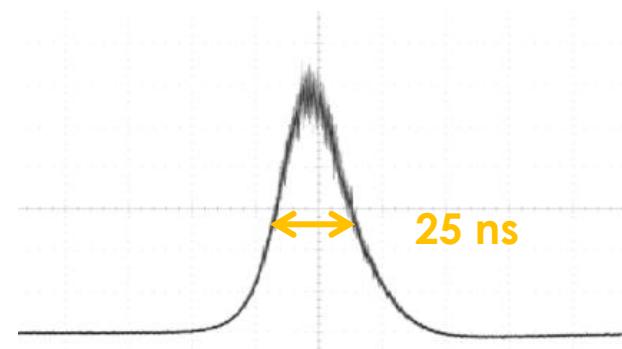


Master oscillator

■ AO tunable & Q-switched laser with Tm-doped fiber

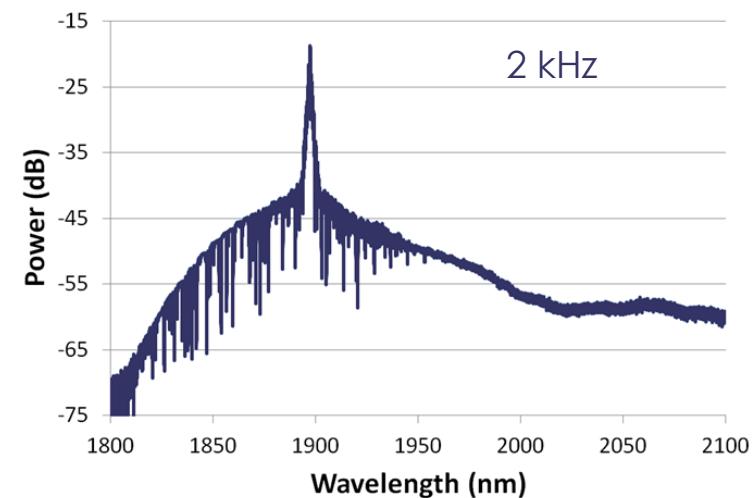
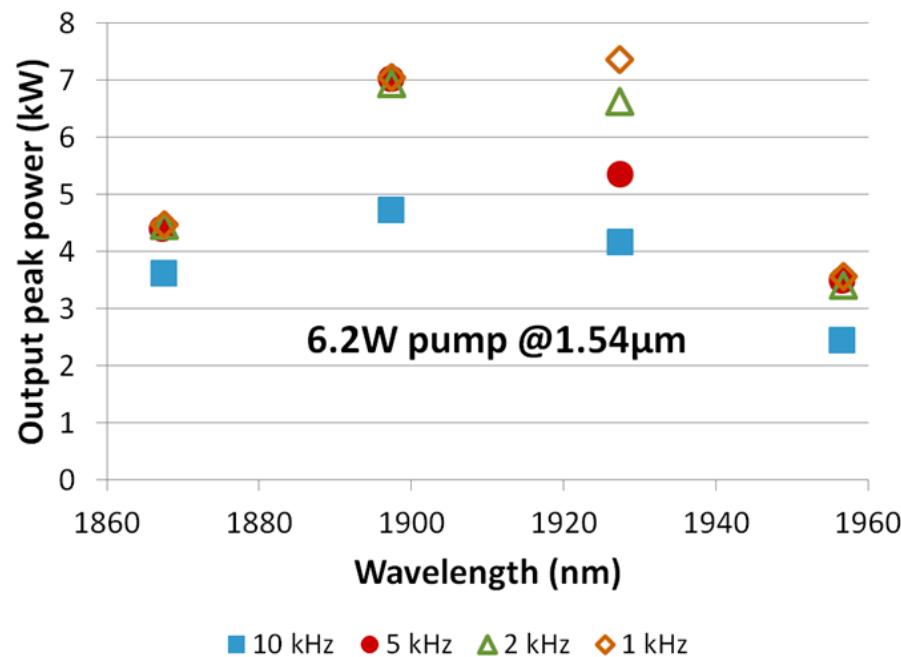
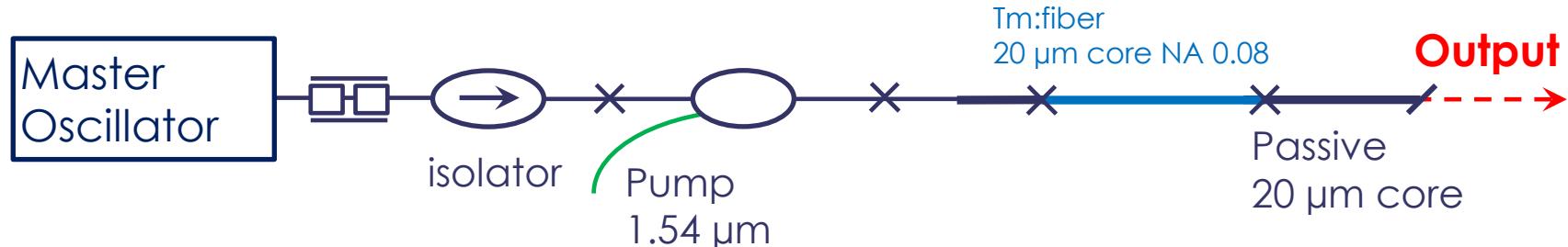


- Q-switch pulses / repetition rate 1-20 kHz
- Pulse width < 35 ns
- Tunability > 90 nm
- Output peak power > 300 W



Fiber amplifier

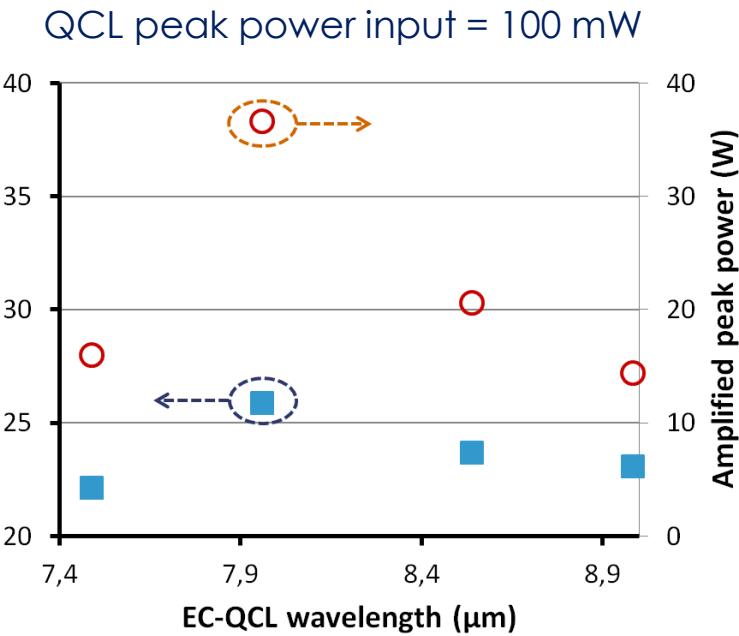
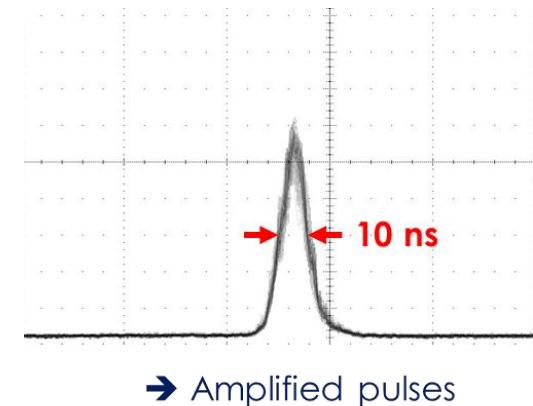
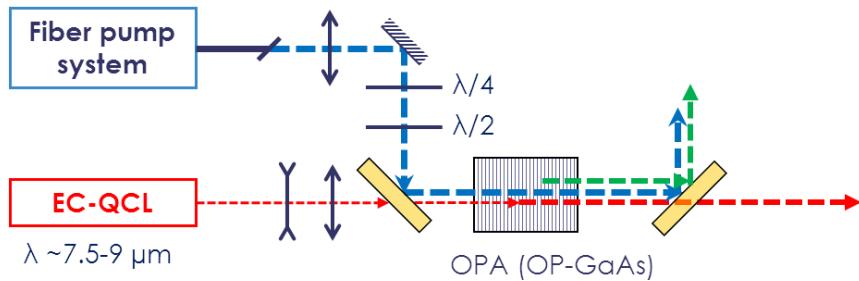
■ 20 µm core diameter amplification stage



- 50-75% of power within 2 nm
- $M^2 < 1.1$

Tunable OPA

- OP-GaAs crystal of period 63.8 μm , length 32 mm, non-optimized AR coatings
- Equal waists for the QCL and the pump
- Experiment at 2 kHz for QCL and pump
- 330 ns QCL pulses synchronized with 25-35 ns pump pulses
- Gain 22-26 dB.
- 15 to 37 W output peak power
- $M^2 < 1.4$



Conclusions

| OPGaAs is a promising material for frequency conversion of 2 µm laser in the Mid-IR spectral range

| 2 µm fiber lasers and amplifiers are the preferred pump source

| However care should be taken to provide:

- All-fiber systems
- Single-spatial mode operation
- Linewidth control

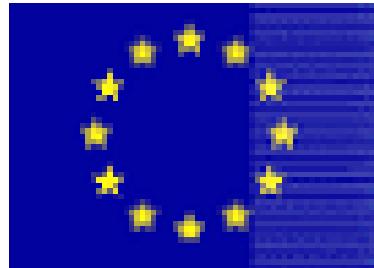
| Thales research & Technology is open for future collaborations in the field

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Acknowledgment

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- > A. Grisard
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- > B. Gerard

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- > M. Eichhorn



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| U of Dusseldorf

| ORC Southampton